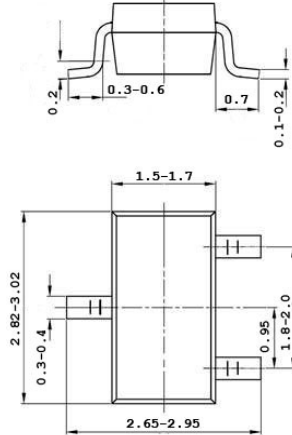
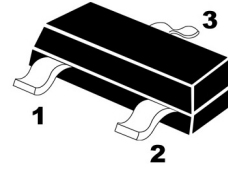


TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

- Low noise: NF = 1dB(Typ.), 10dB(Max.)
- Complementary to 2SC2712
- Small package

MARKING: SO, SY, SG
SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	150	mA
Total Device Dissipation	P_D	150	mW
Junction and Storage Temperature	T_J, T_{stg}	-55-125	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	70		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.3	V
Transition Frequency	f_T	$V_{CE}=-10V, I_C=-1mA$	80			MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			7	pF
Noise Figure	NF	$V_{CE}=-6V, I_C=0.1mA, f=1KHz, R_g=10K\Omega$			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR(G)
Range	70-140	120-240	200-400

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